

SL210A SCHOTTKY RECTIFIER

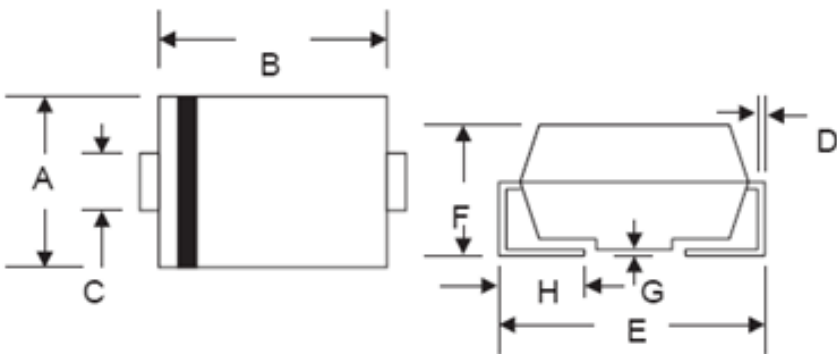
Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

Features:

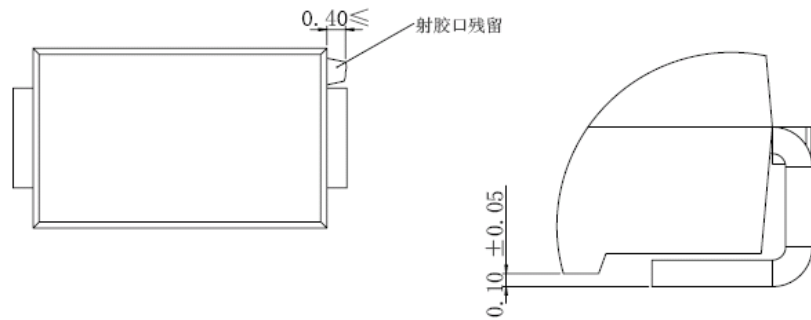
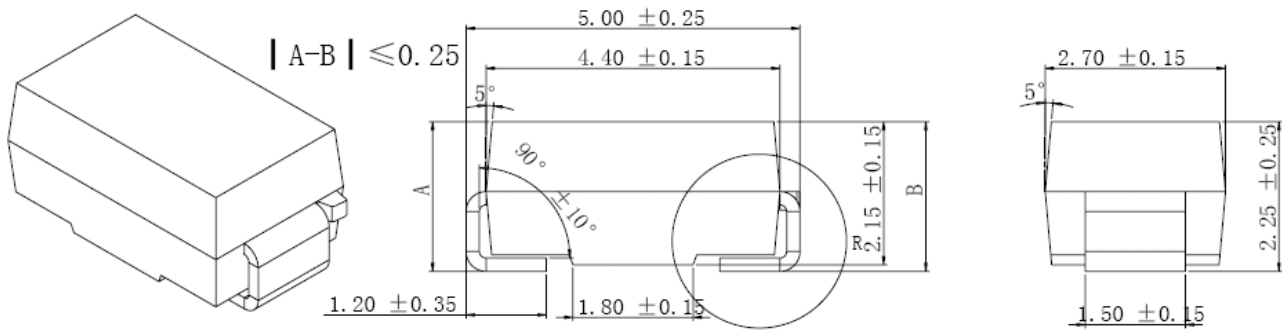
- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In Inches / mm



SMA/DO-214AC				
Dim	Min	Max	Min	Max
A	2.50	2.90	0.098	0.114
B	4.00	4.60	0.157	0.181
C	1.40	1.60	0.055	0.063
D	0.152	0.305	0.006	0.012
E	4.80	5.28	0.189	0.208
F	2.00	2.44	0.079	0.096
G	0.051	0.203	0.002	0.008
H	0.76	1.52	0.030	0.060
	In mm		In inch	

OPTION 1

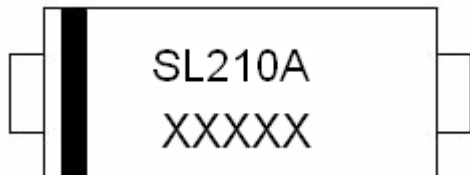


OPTION 2(JK)

SMA

Marking Diagram:

Where XXXXX is YYWWL



- SL = Device Type
- 2 = Forward Current (2A)
- 10 = Reverse Voltage (100V)
- A = Package type
- YY = Year
- WW = Week
- L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SL210A	SMA (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	100	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C=115^\circ\text{C}$, rectangular wave form	2	A
peak one cycle Non-repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse	70	A



Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop *	V _{F1}	@ 2A, Pulse, T _J = 25 °C	0.78	V
	V _{F2}	@ 2A, Pulse, T _J = 125 °C	0.68	V
Reverse Current *	I _{R1}	@V _R = rated V _R T _J = 25 °C	0.1	mA
	I _{R2}	@V _R = rated V _R T _J = 100 °C	2.0	mA
Junction Capacitance	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	200	pF

* Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T _J	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Lead	R _{θJL}	-	17	°C/W
Maximum Thermal Resistance, Junction to Ambient	R _{θJA}	-	75	°C/W
Approximate Weight	wt	-	0.11	g
Case Style	SMA			

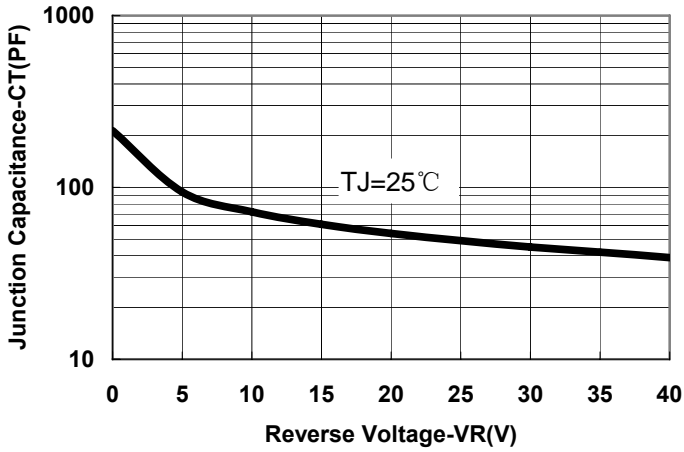


Fig.1-Typical Junction Capacitance Vs. Reverse Voltage

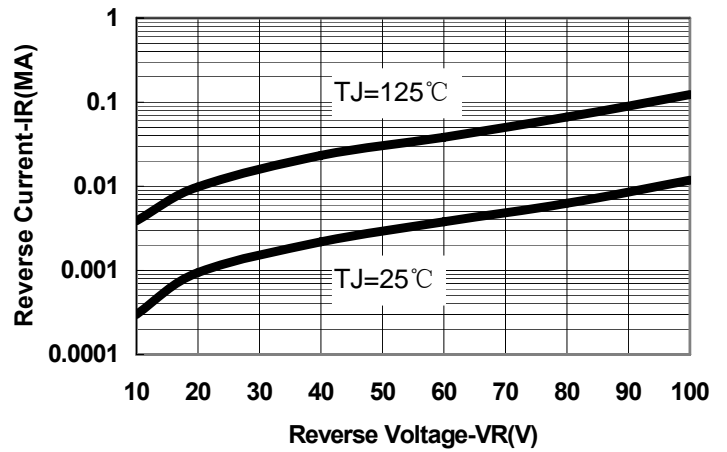


Fig.2-Typical Values Of Reverse Current Vs. Reverse Voltage

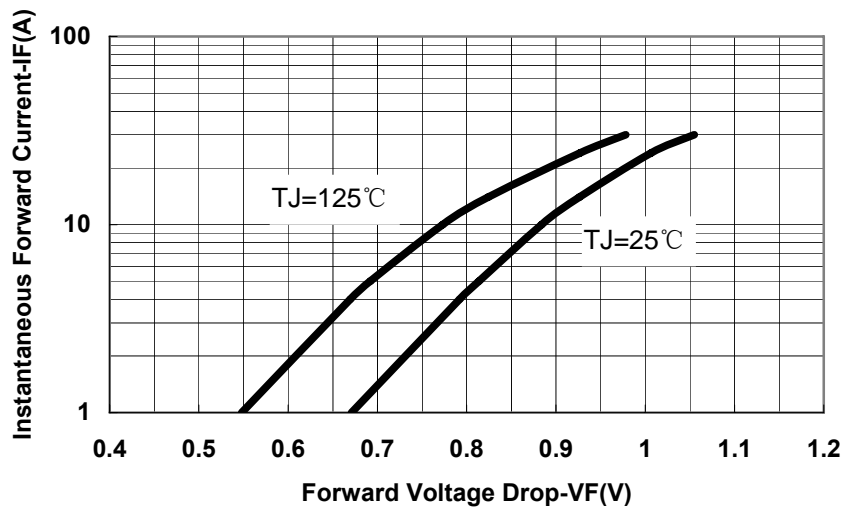


Fig.3-Typical Forward Voltage Drop Characteristics



SL210A

Technical Data
Data Sheet N1347, Rev. -

Green Products

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